

SKiiP[®] 3

2-pack-integrated intelligent Power System

SKiiP 2413 GB123-4DW V3

Features

- SKiiP technology inside
- Trench IGBTs
- CAL HD diode technology
- Integrated current sensor
- Integrated temperature sensor
- Integrated heat sink
- UL recognized File no. E63532

Typical Applications*

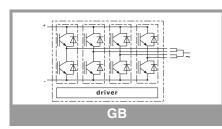
- Renewable energies
- Traction
- Elevators
- Industrial drives

Footnotes

¹⁾ With assembly of suitable MKP capacitor per terminal

Absolute	Maximum Ratin	gs	$T_s = 25^{\circ}C$ unless otherwis	e specified	
Symbol	Conditions		Values	Unit	
System					
V _{CC} ¹⁾	Operating DC lin	k voltage	900	V	
V _{isol}	DC, t = 1 s, main	terminals to heat sink	4300	V	
I _{t(RMS)}	per AC terminal,	T _{terminal} <115°C	400	А	
I _{FSM}	$T_{i} = 150 \text{ °C}, t_{p} = 10 \text{ ms}, \sin 180^{\circ}$		13500	А	
l²t	T _i = 150 °C, t _p = 10 ms, diode		911	kA²s	
f _{out}	fundamental output frequency		1	kHz	
T _{stg}	storage temperature		-40 85	°C	
IGBT					
V _{CES}	T _j = 25 °C		1200	V	
I _C	T _j = 150 °C	T _s = 25 °C	2280	А	
		T _s = 25 °C T _s = 70 °C	1756	Α	
I _{Cnom}			2400	Α	
Tj	junction tempera	ture	-40 150	°C	
Diode			•		
V _{RRM}	T _j = 25 °C		1200	V	
l _F	T 150.90	T _s = 25 °C	1807	Α	
	−T _j = 150 °C	T _s = 70 °C	1370	A	
I _{Fnom}	_	1	1860	Α	
Tj	junction temperature		-40 150		
Driver					
Vs	power supply		13 30	V	
V _{iH}	input signal volta	ge (high)	15 + 0.3	V	
VisoIPD	QPD <= 10pC, P	RIM to POWER	1170	V	
dv/dt	secondary to pri		75	kV/μs	
f _{sw}	switching frequency		8	kHz	

Characte	Characteristics T		T _s = 25°C u	$T_s = 25^{\circ}C$ unless otherwise specified				
Symbol	Conditions		min.	typ.	max.	Unit		
IGBT								
V _{CE(sat)}	I _C = 1200 A	T _j = 25 °C		1.7	2.1	V		
	at terminal	T _j = 125 °C		1.9		V		
V _{CE0}		T _j = 25 °C		0.90	1.10	V		
		T _j = 125 °C		0.80	1.00	V		
r _{CE}	at terminal	T _j = 25 °C		0.7	0.8	mΩ		
		T _j = 125 °C		0.9	1.1	mΩ		
$E_{on} + E_{off}$	I _C = 1200 A	$V_{CC} = 600 V$		442		mJ		
	T _j = 125 °C	V _{CC} = 900 V		780		mJ		
R _{th(j-s)}	per IGBT switch	•			0.015	K/W		
R _{th(j-r)}	per IGBT switch				0.0175	K/W		





SKiiP[®] 3

2-pack-integrated intelligent Power System

SKiiP 2413 GB123-4DW V3

Features

- SKiiP technology inside
- Trench IGBTs
- CAL HD diode technology
- Integrated current sensor
- Integrated temperature sensor
- Integrated heat sink
- UL recognized File no. E63532

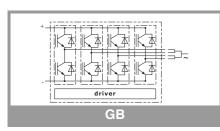
Typical Applications*

- Renewable energies
- Traction
- Elevators
- Industrial drives

Footnotes

¹⁾ With assembly of suitable MKP capacitor per terminal

Characte	ristics	I	$\Gamma_s = 25^{\circ}C$ unless otherwise specified				
Symbol	Conditions		min.	typ.	max.	Unit	
Diode							
$V_F = V_{EC}$	I _F = 1200 A	T _j = 25 °C		1.50	1.80	V	
	at terminal	T _j = 125 °C		1.50		V	
V _{F0}		T _j = 25 °C		0.9	1.10	V	
		T _j = 125 °C		0.7	0.90	V	
r _F	at terminal	T _j = 25 °C		0.5	0.6	mΩ	
		T _j = 125 °C		0.7	0.8	mΩ	
E _{rr}	I _F = 1200 A	V _R = 600 V		84		mJ	
	T _j = 125 °C	V _R = 900 V		112		mJ	
R _{th(j-s)}	per diode switch	•			0.029	K/W	
R _{th(j-r)}	per diode switch				0.045	K/W	
Driver	•		1				
Vs	supply voltage non	stabilized	13	24	30	V	
I _{S0}	bias current @V _s =2	$P_{4V}, f_{sw} = 0, I_{AC} = 0$		330		mA	
ls	$k_1 = 55 \text{ mA/kHz}, k_2$		= 330	$+ k_1 * f_{sw}$	$+ k_2 * I_{AC}^2$	mA	
V _{IT+}	input threshold volt	age (HIGH)	12.3			V	
V _{IT-}	input threshold volt	age (LOW)			4.6	V	
R _{IN}	input resistance			10		kΩ	
CIN	input capacitance		1		nF		
t _{pRESET}	error memory reset time			0.0122		ms	
t _{TD}	top / bottom switch interlock time			3		μs	
t _{jitter}	jitter clock time			125		ns	
t _{SIS}	short pulse suppression time			0.625	0.7	μs	
ITRIPSC	over current trip level		2940	3000	3060	A _{PEAK}	
T _{trip}	over temperature trip level		110	115	120	°C	
V _{DCtrip}	over voltage trip level,			not impl.		V	
t _{d(on)IO}	V _{CC} = 900 V	input-output turn-on propagation time		1.4		μs	
t _{d(off)IO}	$T_j = 25 °C$	input-output turn-off propagation time		1.4		μs	
System							
R _{th(r-a)}	flow rate=8l/min, T _F glycol ratio 50%:50	%			0.0092	K/W	
R _{CC'+EE'}	measured per swite			0.13		mΩ	
L _{CE}	commutation induc			3		nH	
C _{CHC}	per phase, AC-side			6.8		nF	
$I_{CES} + I_{RD}$	$V_{GE} = 0 V, V_{CE} = 12$			4.8		mA	
M _{dc}	DC terminals, SI Ur		6		8	Nm	
M _{ac}	AC terminals, SI Ur		13		15	Nm	
W	SKiiP System w/o h	neat sink		3.1		kg	
Wh	heat sink			6.2		kg	



solation coordination acc. to EN 50178 and IEC 61800-5-1	
Maximum grid RMS voltage, line-to-line, grounded delta mains	480V+20%
Installation altitude for maximum grid RMS voltage, line-to-line, grounded delta mains	2000m
Maximum grid RMS voltage, line-to-line, star point grounded mains	480V+20%
Installation altitude for maximum grid RMS voltage, line-to-line, star point grounded mains	5000m
Maximum transient peak voltage between low voltage circuit and mains	1600V
Pollution degree acc. to IEC 60664-1 outside the moulded power section	2
Overvoltage cat. acc. to IEC 60664-1 for mains	111
Basic isolation	between heat sink and mains; between low voltage circuit and mains
Protection level acc. to IEC 60529	IP00

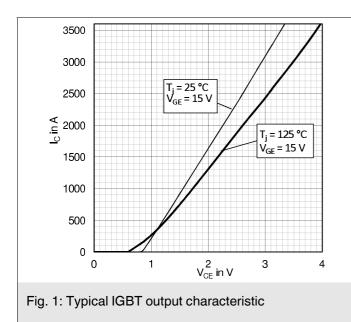
	Storage	Transportation	Operation stationary use at weather protected locations	Operating ground vehicle installations	Operating ship environment
Climatic conditions	1K2 ₍₁₎	2K2 ₍₁₎	3K3 ₍₁₎	5K1 ₍₁₎	
Biological conditions	1B1	2B1	3B1	5B1	6B1
Chemically active substances (excluded: salt spray)	1C2	2C1	3C2	5C2	6C2
Mechanically active substances	1S1	281	3S1	581	6S1
Mechanical conditions	1M3	(4)	3M6 ₍₂₎	5M3 ₍₃₎	6M3
Contaminating fluids				5F1	

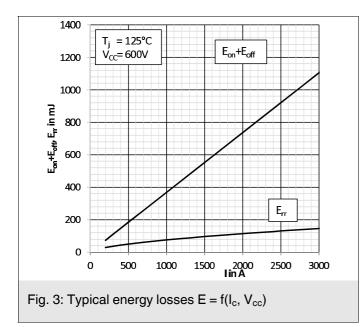
(1) expanded temperature range: -40°C / +85°C. Please note: by operation near 85°C the life time of product is reduced.

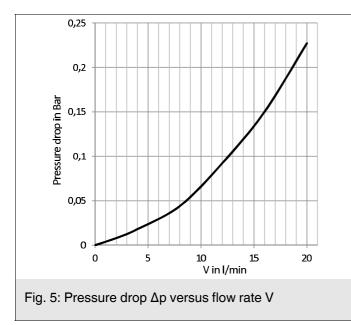
(2) 3M7 possible, but due to the mechanic load capacity of external components like DC-Link capacitors limited to 3M6

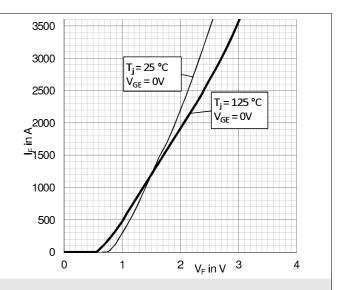
(3) 5M3 without impact of foreign bodies, stones

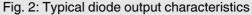
(4) no declaration due to customer-specific packing

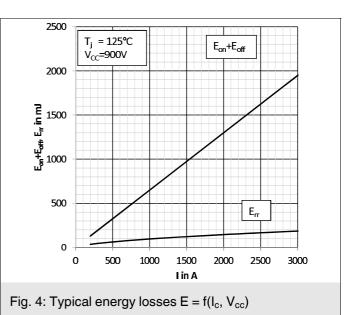












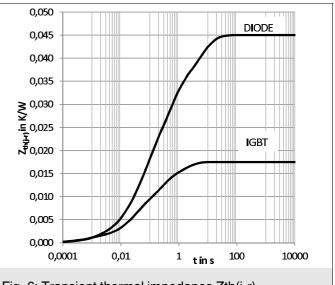
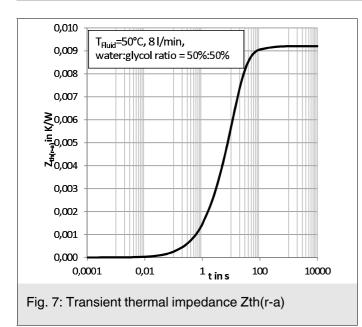
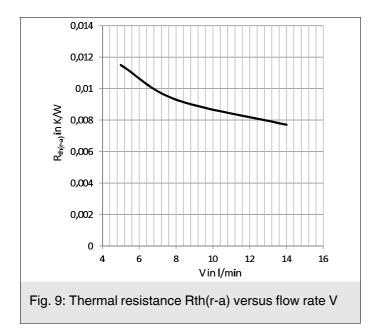
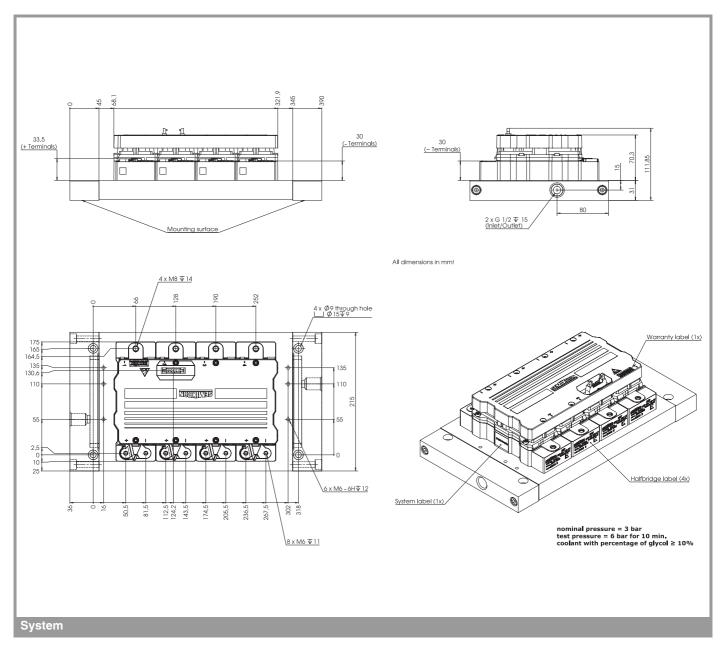


Fig. 6: Transient thermal impedance Zth(j-r)





	Rth [K/W]								
	1	2	3	4	5	6			
Zth(j-r) I	0,0011	0,0059	0,0063	0,0021	0,0021	0,0000			
Zth(j-r) D	0,0011	0,0042	0,0129	0,0150	0,0094	0,0024			
Zth(r-a)	0,0002	0,0012	0,0042	0,0034	0,0002	0,0000			
		tau [s]							
	1	2	3	4	5	6			
Zth(j-r) I	0,0007	0,0268	0,2165	1,0453	2,2456	1,0000			
Zth(j-r) D	0,0013	0,0142	0,0676	0,4902	5,0713	14,977			
Zth(r-a)	0,1382	1,4254	8,3077	20,093	189,77	1,0000			



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, chapter IX.

***IMPORTANT INFORMATION AND WARNINGS**

The specifications of SEMIKRON products may not be considered as guarantee or assurance of product characteristics ("Beschaffenheitsgarantie"). The specifications of SEMIKRON products describe only the usual characteristics of products to be expected in typical applications, which may still vary depending on the specific application. Therefore, products must be tested for the respective application in advance. Application adjustments may be necessary. The user of SEMIKRON products is responsible for the safety of their applications embedding SEMIKRON products and must take adequate safety measures to prevent the applications from causing a physical injury, fire or other problem if any of SEMIKRON products become faulty. The user is responsible to make sure that the application design is compliant with all applicable laws, regulations, norms and standards. Except as otherwise explicitly approved by SEMIKRON in a written document signed by authorized representatives of SEMIKRON, SEMIKRON products may not be used in any applications where a failure of the product or any consequences of the use thereof can reasonably be expected to result in personal injury. No representation or warranty is given and no liability is assumed with respect to the accuracy, completeness and/or use of any information herein, including without limitation, warranties of non-infringement of intellectual property rights of any third party. SEMIKRON does not assume any liability arising out of the applications or use of any product; neither does it convey any license under its patent rights, copyrights, trade secrets or other intellectual property rights, nor the rights of others. SEMIKRON makes no representation or warranty of non-infringement or alleged non-infringement of intellectual property rights of any third party which may arise from applications. Due to technical requirements our products may contain dangerous substances. For information on the types in question please contact the nearest SEMIKRON sales office. This document supersedes and replaces all information previously supplied and may be superseded by updates. SEMIKRON reserves the right to make changes.